

## Fast Recovery Diodes (Hockey PUK Version), 920/1050 A



DO-200AB (B-PUK)

**FEATURES**

- High power fast recovery diode series
- 2.0  $\mu$ s to 3.0  $\mu$ s recovery time
- High voltage ratings up to 3000 V
- High current capability
- Optimized turn-on and turn-off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press PUK encapsulation
- Case style conform to JEDEC® DO-200AB (B-PUK)
- Maximum junction temperature 150 °C
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS  
COMPLIANT**
**PRODUCT SUMMARY**

$I_{F(AV)}$	920 A to 1050 A
Package	DO-200AB (B-PUK)
Circuit configuration	Single Diode

**TYPICAL APPLICATIONS**

- Snubber diode for GTO
- High voltage freewheeling diode
- Fast recovery rectifier applications

**MAJOR RATINGS AND CHARACTERISTICS**

PARAMETER	TEST CONDITIONS	SD1053C..L		UNITS
		S20	S30	
$I_{F(AV)}$		1050	920	A
	$T_{hs}$	55	55	°C
$I_{F(RMS)}$		1940	1700	A
$I_{FSM}$	50 Hz	15 000	13 000	
	60 Hz	15 700	13 610	
$V_{RRM}$	Range	1800 to 2500	1800 to 3000	V
$t_{rr}$		2.0	3.0	$\mu$ s
	$T_J$	25		°C
$T_J$	-40 to 150			

**ELECTRICAL SPECIFICATIONS**
**VOLTAGE RATINGS**

TYPE NUMBER	VOLTAGE CODE	$V_{RRM}$ , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	$I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-SD1053C..S20L	18	1800	1900	50
	22	2200	2300	
	25	2500	2600	
VS-SD1053C..S30L	18	1800	1900	
	22	2200	2300	
	25	2500	2600	
	28	2800	2900	
	30	3000	3100	



FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		SD1053C..L		UNITS
				S20	S30	
Maximum average forward current at heatsink temperature	$I_{F(AV)}$	180° conduction, half sine wave Double side (single side) cooled		1050 (450)	920 (390)	A
				55 (85)	55 (85)	°C
Maximum RMS forward current	$I_{F(RMS)}$	25 °C heatsink temperature double side cooled		1940	1700	
Maximum peak, one-cycle forward, non-repetitive surge current	$I_{FSM}$	t = 10 ms t = 8.3 ms t = 10 ms t = 8.3 ms	No voltage reappplied 100 % $V_{RRM}$ reappplied Sinusoidal half wave, initial $T_J = T_J$ maximum	15 000	13 000	A
				15 700	13 610	
				12 620	10 930	
				13 210	11 450	
Maximum $I^2t$ for fusing	$I^2t$	t = 10 ms t = 8.3 ms t = 10 ms t = 8.3 ms	No voltage reappplied 100 % $V_{RRM}$ reappplied	1125	845	kA <sup>2</sup> s
				1027	772	
				796	598	
				727	546	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reappplied		11 250	8450	kA <sup>2</sup> √s
Low level value of threshold voltage	$V_{F(TO)1}$	(16.7 % $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$ , $T_J = T_J$ maximum)		1.34	1.51	V
High level value of threshold voltage	$V_{F(TO)2}$	(I > $\pi \times I_{F(AV)}$ , $T_J = T_J$ maximum)		1.48	1.67	
Low level value of forward slope resistance	$r_{f1}$	(16.7 % $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$ , $T_J = T_J$ maximum)		0.37	0.50	mΩ
High level value of forward slope resistance	$r_{f2}$	(I > $\pi \times I_{F(AV)}$ , $T_J = T_J$ maximum)		0.33	0.45	
Maximum forward voltage drop	$V_{FM}$	$I_{pk} = 1500$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sinusoidal wave		1.90	2.26	V

RECOVERY CHARACTERISTICS								
CODE	MAXIMUM VALUE AT $T_J = 25$ °C	TEST CONDITIONS			TYPICAL VALUES AT $T_J = 150$ °C			
	$t_{rr}$ AT 25 % $I_{RRM}$ (μs)	$I_{pk}$ SQUARE PULSE (A)	dI/dt (A/μs)	$V_r$ (V)	$t_{rr}$ AT 25 % $I_{RRM}$ (μs)	$Q_{rr}$ (μC)	$I_{rr}$ (A)	
S20	2.0	1000	100	- 50	4.0	400	180	
S30	3.0				4.5	550	230	

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range	$T_J, T_{Stg}$		-40 to 150	°C
Maximum thermal resistance, case junction to heatsink	$R_{thJ-hs}$	DC operation single side cooled	0.073	K/W
		DC operation double side cooled	0.031	
Mounting force, ± 10 %			14 700 (1500)	N (kg)
Approximate weight			255	g
Case style		See dimensions - link at the end of datasheet	DO-200AB (B-PUK)	

$\Delta R_{thJ-hs}$ CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.009	0.008	0.006	0.006	$T_J = T_J$ maximum	K/W
120°	0.011	0.011	0.011	0.011		
90°	0.014	0.014	0.015	0.015		
60°	0.020	0.021	0.021	0.022		
30°	0.036	0.036	0.036	0.036		

Note

- The table above shows the increment of thermal resistance  $R_{thJ-hs}$  when devices operate at different conduction angles than DC

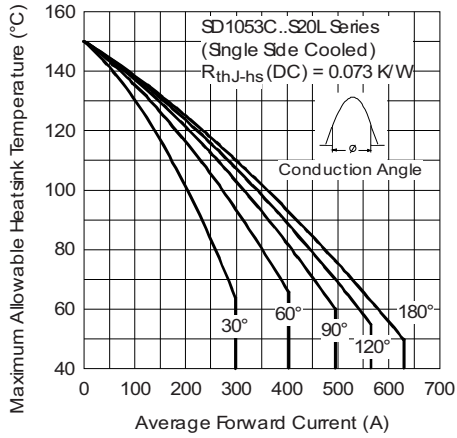


Fig. 1 - Current Ratings Characteristics

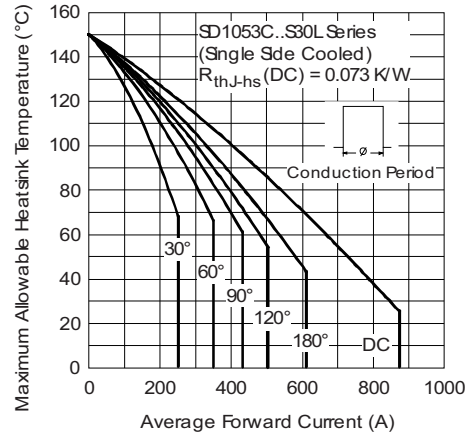


Fig. 4 - Current Ratings Characteristics

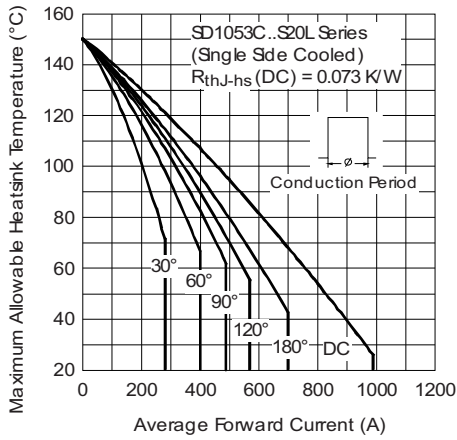


Fig. 2 - Current Ratings Characteristics

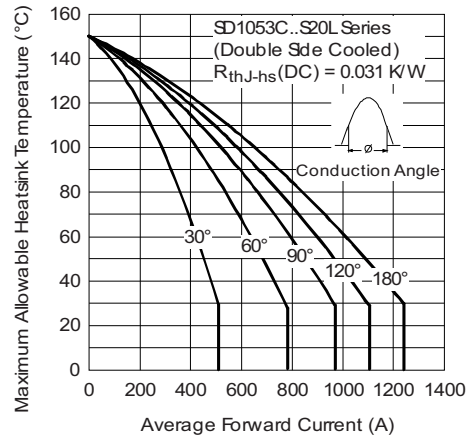


Fig. 5 - Current Ratings Characteristics

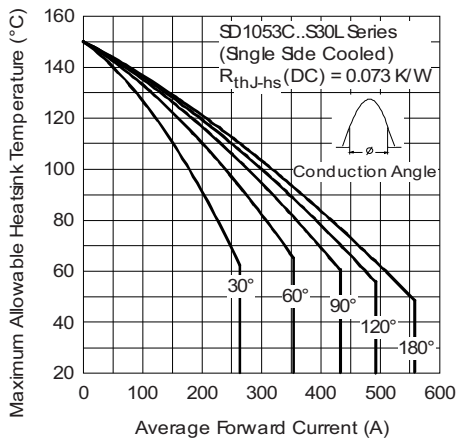


Fig. 3 - Current Ratings Characteristics

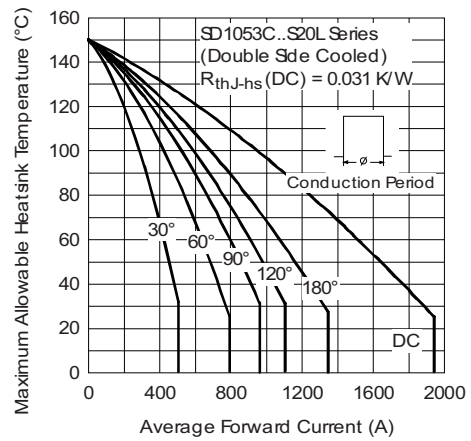


Fig. 6 - Current Ratings Characteristics

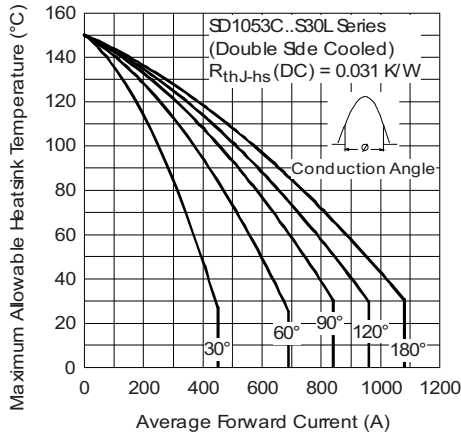


Fig. 7 - Current Ratings Characteristics

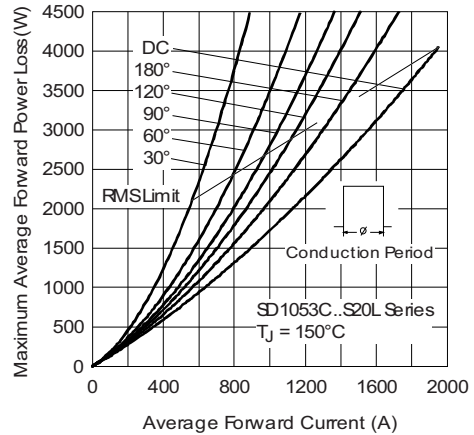


Fig. 10 - Forward Power Loss Characteristics

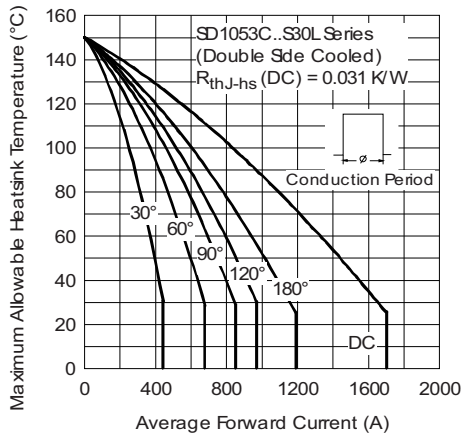


Fig. 8 - Current Ratings Characteristics

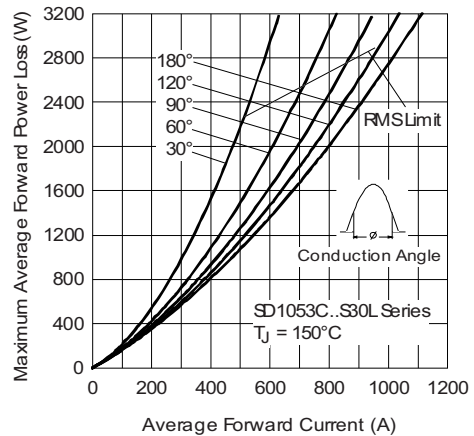


Fig. 11 - Forward Power Loss Characteristics

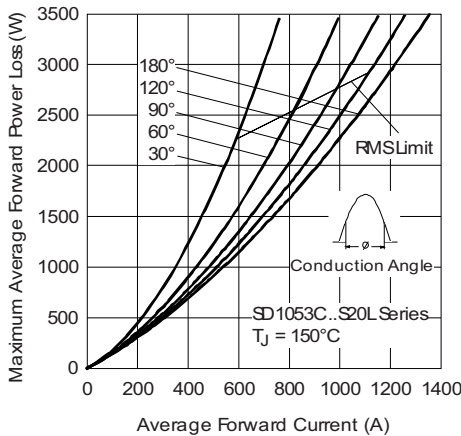


Fig. 9 - Forward Power Loss Characteristics

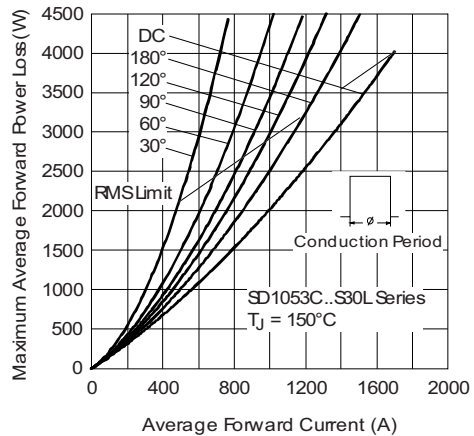


Fig. 12 - Forward Power Loss Characteristics

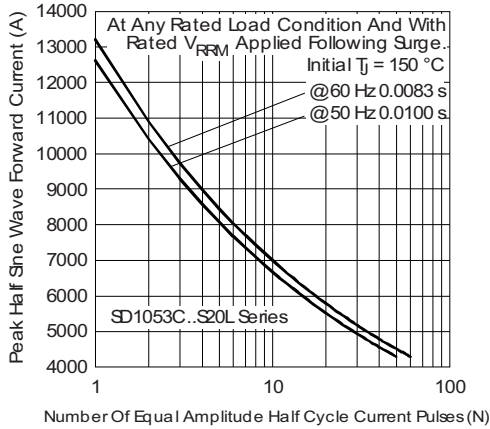


Fig. 13 - Maximum Non-Repetitive Surge Current

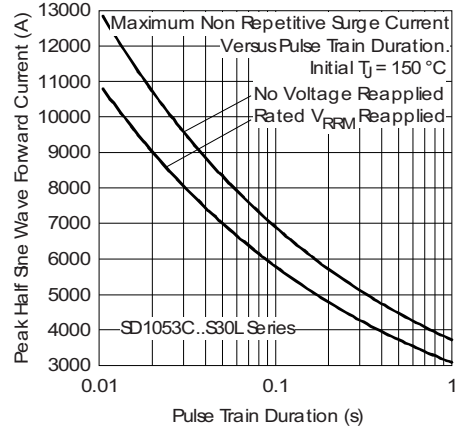


Fig. 16 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

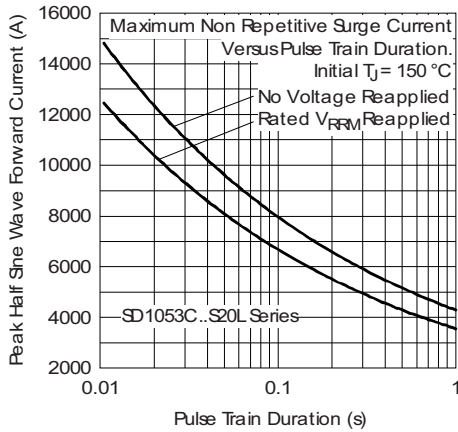


Fig. 14 - Maximum Non-Repetitive Surge Current

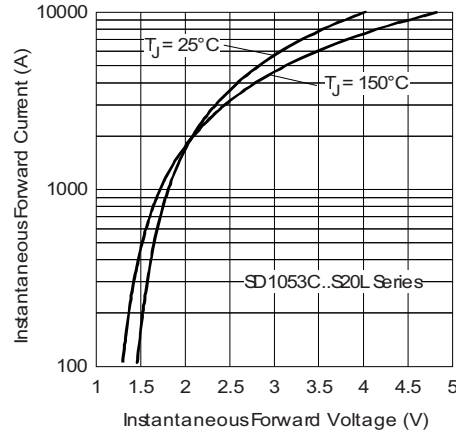


Fig. 17 - Forward Voltage Drop Characteristics

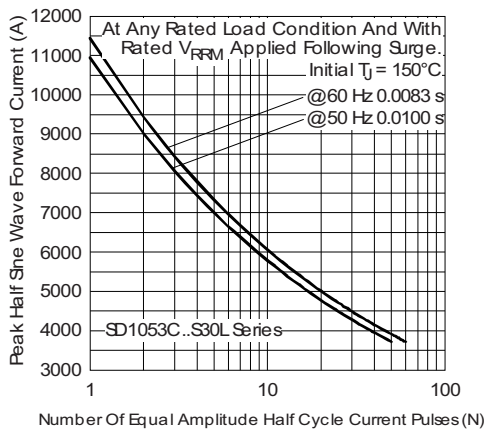


Fig. 15 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

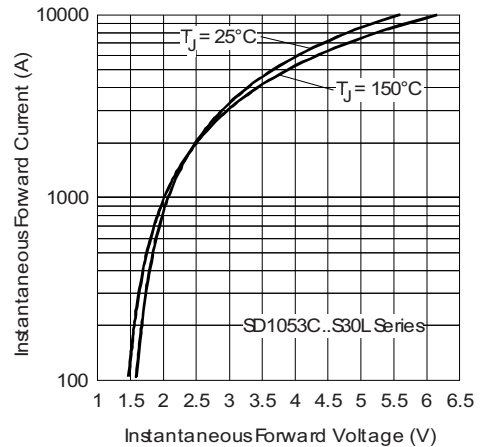


Fig. 18 - Forward Voltage Drop Characteristics

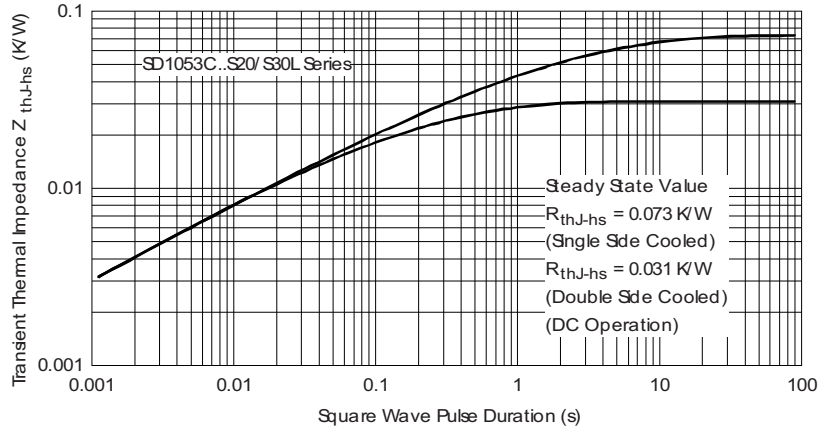


Fig. 19 - Thermal Impedance  $Z_{thJ-hs}$  Characteristic

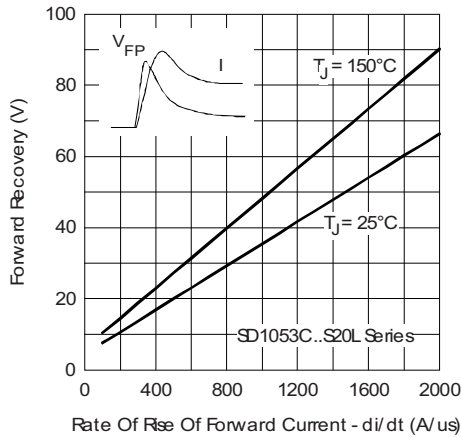


Fig. 20 - Typical Forward Recovery Characteristics

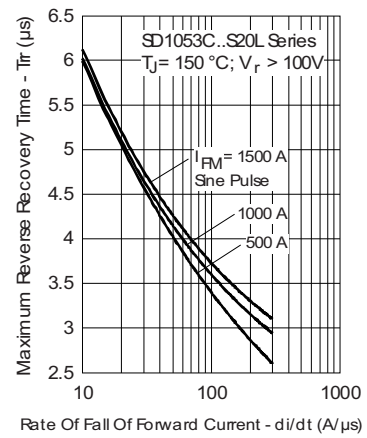


Fig. 22 - Recovery Time Characteristics

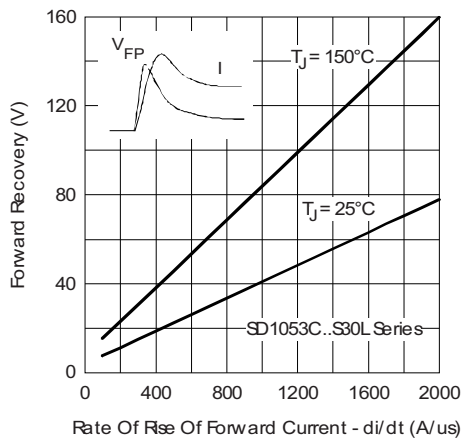


Fig. 21 - Typical Forward Recovery Characteristics

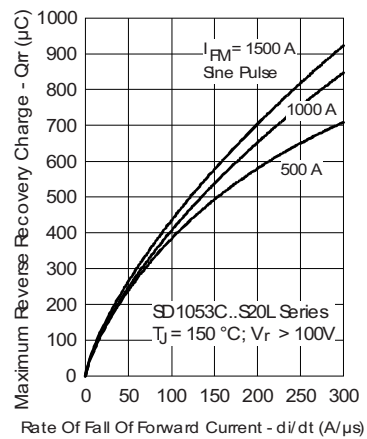


Fig. 23 - Recovery Charge Characteristics

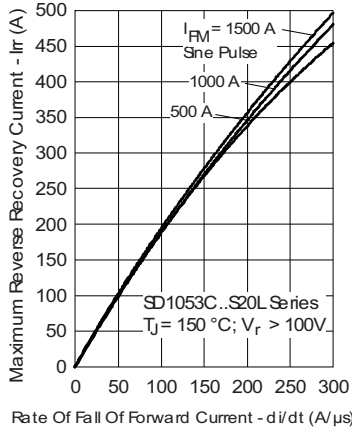


Fig. 24 - Recovery Current Characteristics

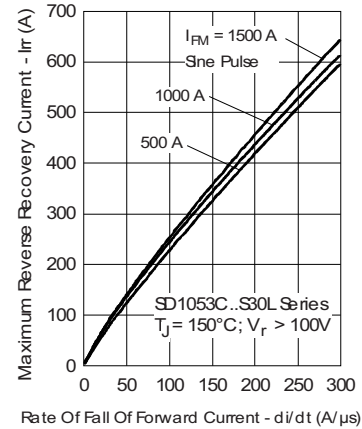


Fig. 27 - Recovery Current Characteristics

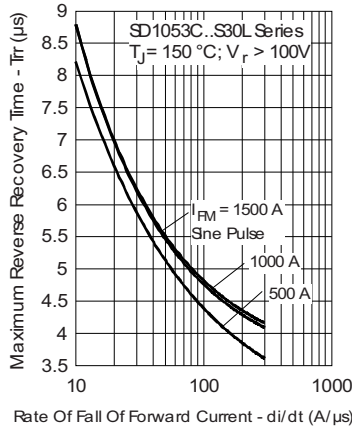


Fig. 25 - Recovery Time Characteristics

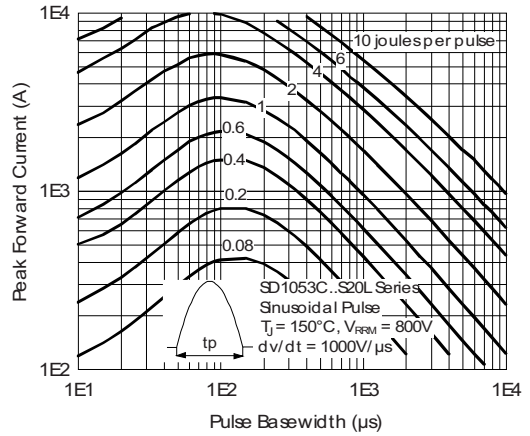


Fig. 28 - Maximum Total Energy Loss Per Pulse Characteristics

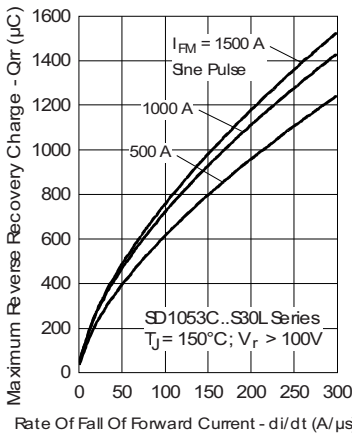


Fig. 26 - Recovery Charge Characteristics

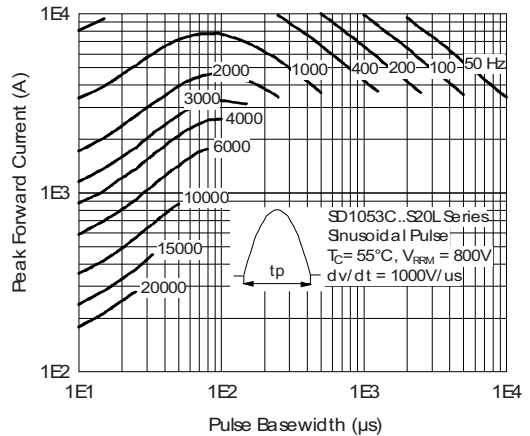


Fig. 29 - Frequency Characteristics

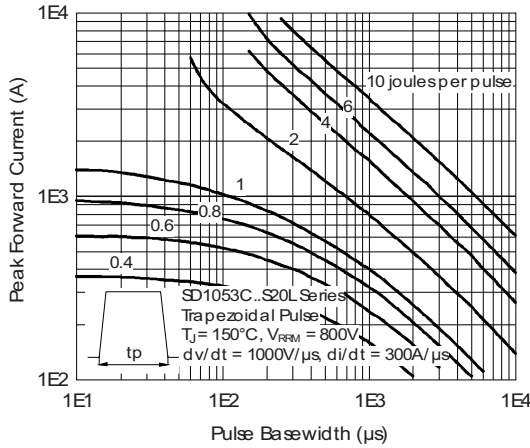


Fig. 30 - Maximum Total Energy Loss Per Pulse Characteristics

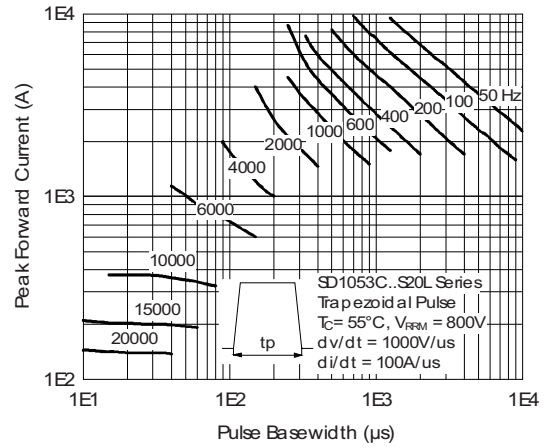


Fig. 33 - Frequency Characteristics

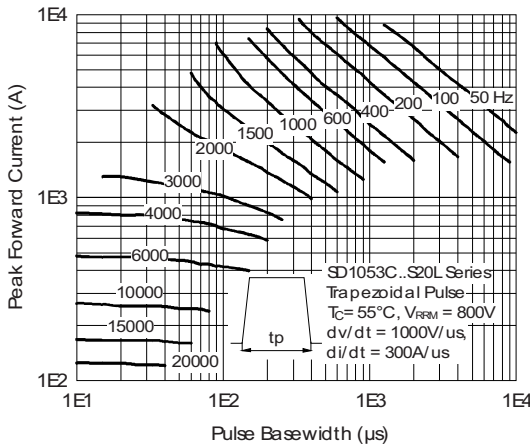


Fig. 31 - Frequency Characteristics

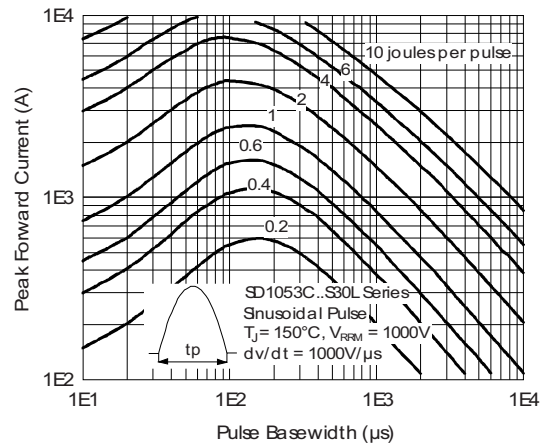


Fig. 34 - Maximum Total Energy Loss Per Pulse Characteristics

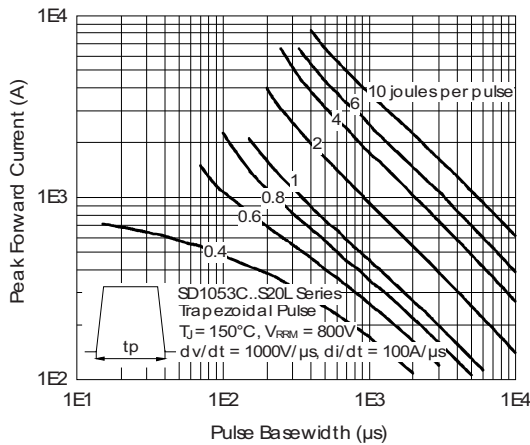


Fig. 32 - Maximum Total Energy Loss Per Pulse Characteristics

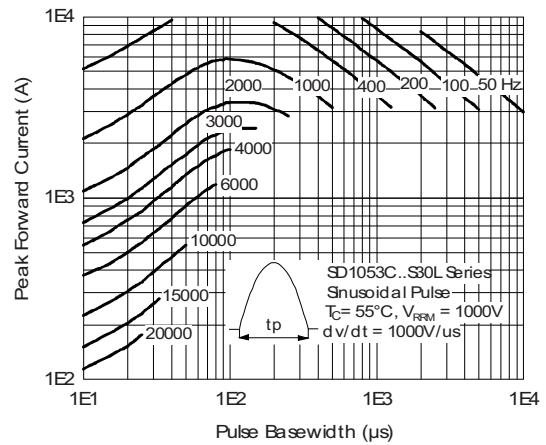


Fig. 35 - Frequency Characteristics



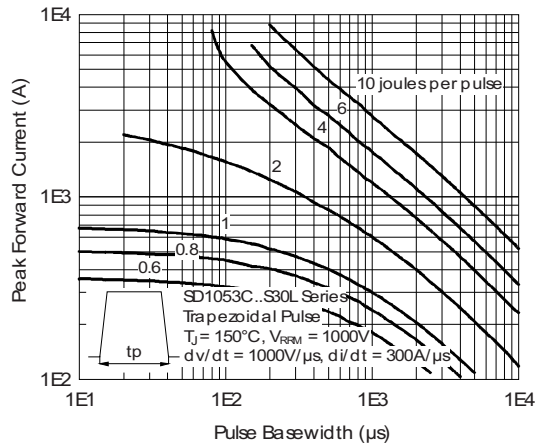


Fig. 36 - Maximum Total Energy Loss Per Pulse Characteristics

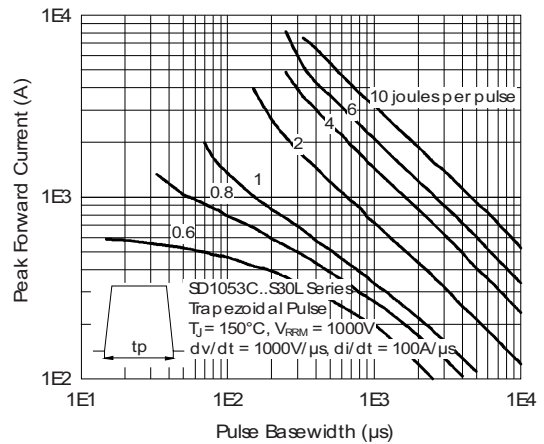


Fig. 38 - Maximum Total Energy Loss Per Pulse Characteristics

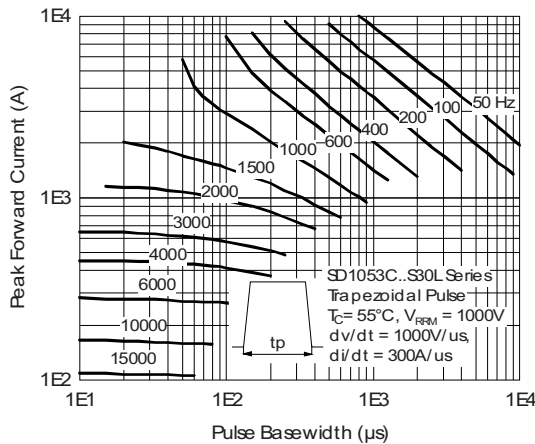


Fig. 37 - Frequency Characteristics

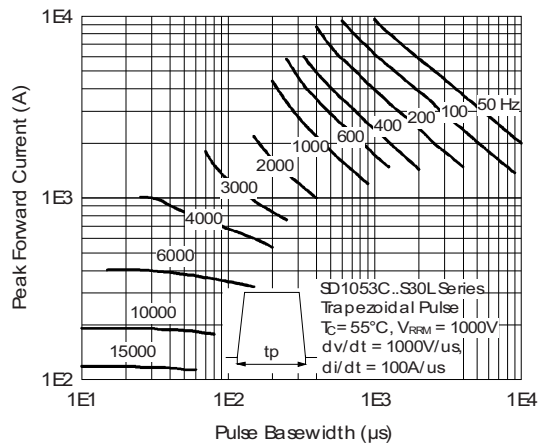


Fig. 39 - Frequency Characteristics

**ORDERING INFORMATION TABLE**

Device code	<b>VS-</b>	<b>SD</b>	<b>105</b>	<b>3</b>	<b>C</b>	<b>30</b>	<b>S30</b>	<b>L</b>
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- ①
- ②
- ③
- ④
- ⑤
- ⑥
- ⑦
- ⑧

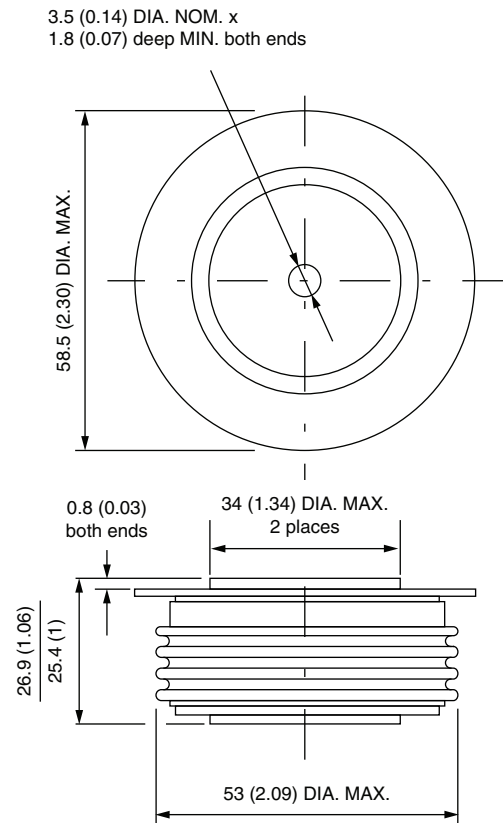
- 1** - Vishay Semiconductors product
- 2** - Diode
- 3** - Essential part number
- 4** - 3 = Fast recovery
- 5** - C = Ceramic PUK
- 6** - Voltage code x 100 =  $V_{RRM}$  (see Voltage Ratings table)
- 7** -  $t_{tr}$  code
- 8** - L = PUK case DO-200AB (B-PUK)

**LINKS TO RELATED DOCUMENTS**

Dimensions	<a href="http://www.vishay.com/doc?95246">www.vishay.com/doc?95246</a>
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## DO-200AB (B-PUK)

**DIMENSIONS** in millimeters (inches)



Quote between upper and lower pole pieces has to be considered after application of mounting force (see Thermal and Mechanical Specifications)



## Disclaimer

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**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.**

**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

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### Вы можете приобрести в компании MosChip.

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<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

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